

MiniSKiiP® 3

IGBT module

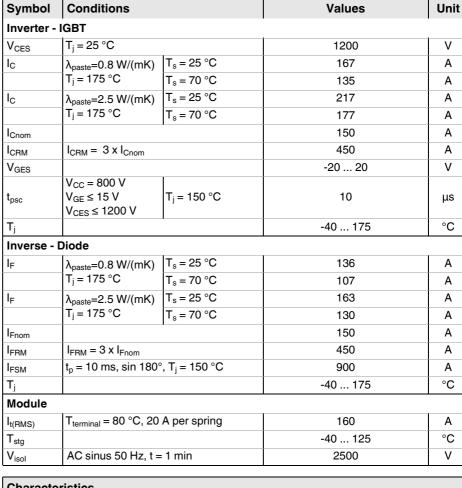
SKiiP 39GA12T4V1

Features

- Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

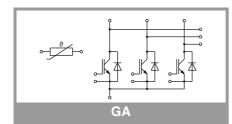
Remarks

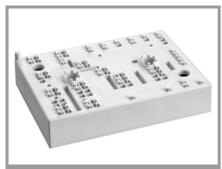
- Max. case temperature limited to T_C=125°C
- Product reliability results valid for T_j≤150°C (recommended T_{j,op}=-40...+150°C)
- Please refer to MiniSKiiP "Technical Explanations" and "Mounting Instructions" for further information



Absolute Maximum Ratings

Characteristics									
Symbol	Conditions	min.	typ.	max.	Unit				
Inverter -	IGBT								
V _{CE(sat)}	I _C = 150 A	T _j = 25 °C		1.85	2.10	V			
	V _{GE} = 15 V chiplevel	T _j = 150 °C		2.25	2.45	V			
V _{CE0}	chiplevel	T _j = 25 °C		0.80	0.90	V			
		T _j = 150 °C		0.70	0.80	V			
r _{CE}	V _{GE} = 15 V chiplevel	T _j = 25 °C		7.0	8.0	mΩ			
		T _j = 150 °C		10	11	mΩ			
$V_{\text{GE(th)}}$	$V_{GE} = V_{CE}$, $I_C = 6$ mA		5	5.8	6.5	V			
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = 12$	00 V, T _j = 25 °C		0.1	0.3	mA			
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		8.80		nF			
C _{oes}		f = 1 MHz		0.58		nF			
C _{res}		f = 1 MHz		0.47		nF			
Q_{G}	- 8 V+ 15 V			850		nC			
R _{Gint}	T _j = 25 °C			5.0		Ω			
t _{d(on)}	$\begin{split} V_{CC} &= 600 \text{ V} \\ I_{C} &= 150 \text{ A} \\ R_{G \text{ on}} &= 1 \Omega \\ R_{G \text{ off}} &= 1 \Omega \\ \text{di/dt}_{on} &= 2840 \text{ A/}\mu\text{s} \\ \text{di/dt}_{off} &= 1880 \text{ A/}\mu\text{s} \end{split}$	T _j = 150 °C		165		ns			
t_{r}		T _j = 150 °C		50		ns			
Eon		T _j = 150 °C		22.5		mJ			
$t_{\text{d(off)}} \\$		T _j = 150 °C		390		ns			
t _f		T _j = 150 °C	80			ns			
E _{off}	V _{GE} = +15/-15 V	T _j = 150 °C		14		mJ			
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(mK)			0.33		K/W			
$R_{th(j-s)}$	per IGBT, λ_{paste} =2.5 W/(mK)			0.21		K/W			





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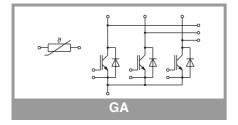
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Characteristics										
Symbol	Conditions	min.	typ.	max.	Unit					
Inverse - Diode										
$V_F = V_{EC}$	$V_F = V_{EC}$ $V_{GE} = 0 V$ $V_{GE} = 0 V$ $V_{GE} = 0 V$	T _j = 25 °C		2.14	2.46	V				
		T _j = 150 °C		2.07	2.38	V				
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V				
		T _j = 150 °C		0.90	1.10	V				
r _F	- chiplevel	T _j = 25 °C		5.6	6.4	mΩ				
		T _j = 150 °C		7.8	8.5	mΩ				
I _{RRM}	$di/dt_{off} = 4020 \text{ A/}\mu\text{s}$ $V_{GE} = +15/-15 \text{ V}$	T _j = 150 °C		188		Α				
Q _{rr}		T _j = 150 °C		27		μC				
E _{rr}		T _j = 150 °C		11.4		mJ				
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			0.52		K/W				
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			0.39		K/W				
Module										
L _{CE}				-		nΗ				
Ms	to heat sink		2		2.5	Nm				
W				82		g				
Temperat	ture Sensor									
R ₁₀₀	T _r =100°C (R ₂₅ =1000Ω)			1670 ± 3%		Ω				
R(T)	R(T)= $1000\Omega[1+A(T-25^{\circ}C)+B(T-25^{\circ}C)^{2}]$, A = $7.635^{*}10^{-3} {^{\circ}C^{-1}}$, B = $1.731^{*}10^{-5} {^{\circ}C^{-2}}$									



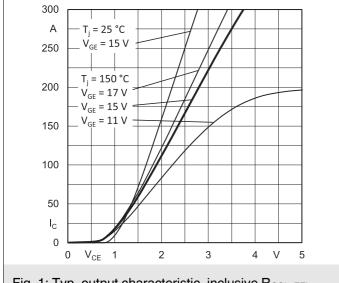


Fig. 1: Typ. output characteristic, inclusive $R_{\text{CC}'\text{+ EE'}}$

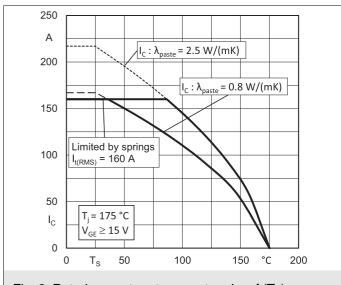


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

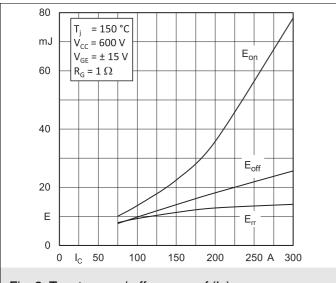


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

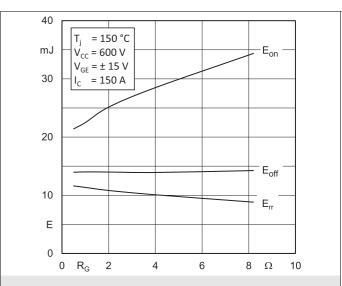


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

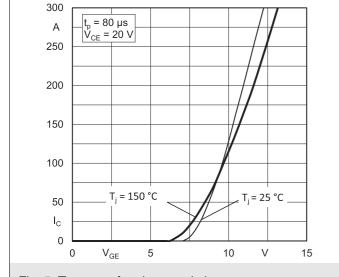


Fig. 5: Typ. transfer characteristic

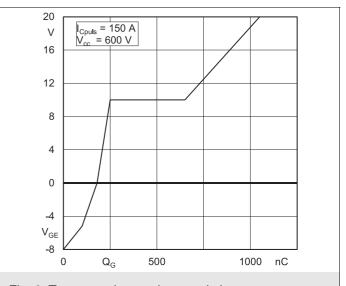


Fig. 6: Typ. gate charge characteristic

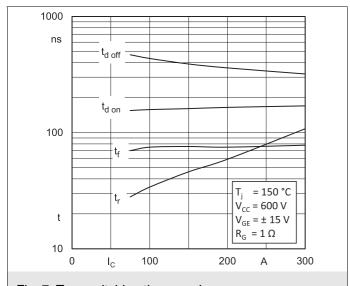


Fig. 7: Typ. switching times vs. I_C

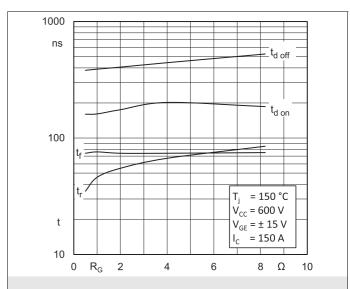


Fig. 8: Typ. switching times vs. gate resistor R_{G}

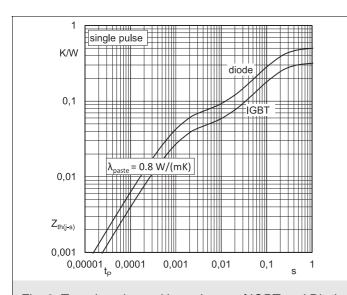


Fig. 9: Transient thermal impedance of IGBT and Diode

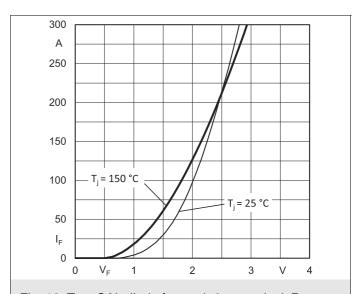


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+\,EE'}$

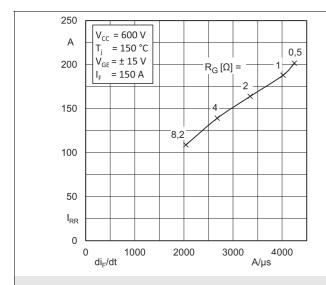


Fig. 11: Typ. CAL diode peak reverse recovery current

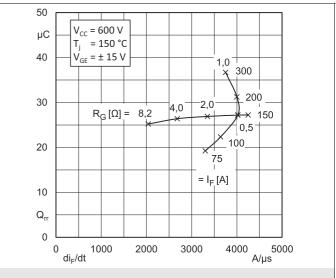
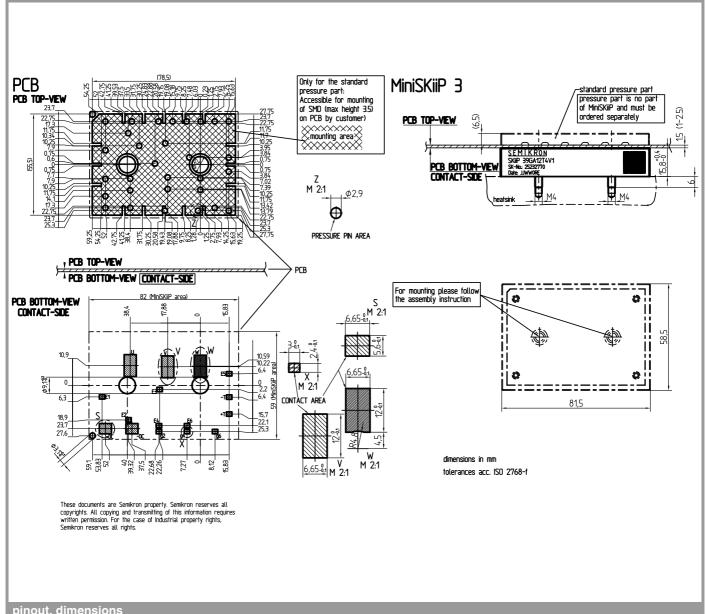
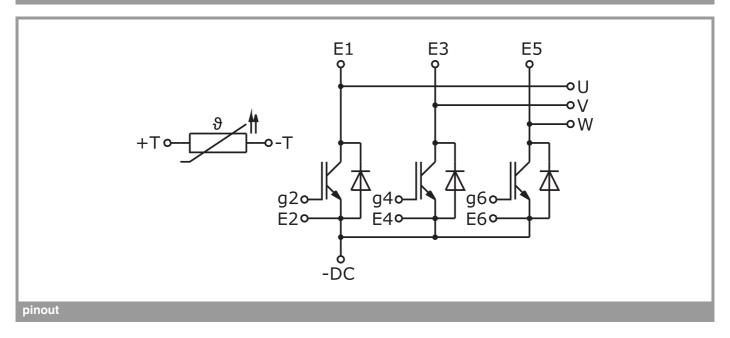


Fig. 12: Typ. CAL diode recovery charge



pinout, dimensions



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

*IMPORTANT INFORMATION AND WARNINGS

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